TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

2SC5029

Power Amplifier Applications
Power Switching Applications

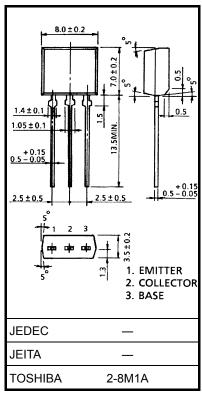
- Low saturation voltage: $V_{CE (sat)} = 0.5 \text{ V (max)} (I_{C} = 1 \text{ A}, I_{B} = 0.05 \text{ A})$
- High collector power dissipation: PC = 1.3 W
- High-speed switching: $t_{stg} = 1.0 \mu s$ (typ.)
- Complementary to 2SA1892

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	IC	3	Α
Base current	ΙΒ	0.2	Α
Collector power dissipation	PC	1.3	W
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in

Industrial Applications
Unit: mm



Weight: 0.55 g (typ.)

temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

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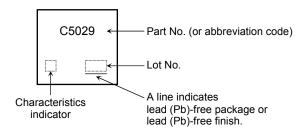


Electrical Characteristics (Ta = 25°C)

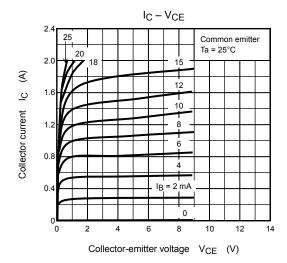
Chara	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off co	urrent	I _{CBO}	V _{CB} = 50 V, I _E = 0	_	_	1.0	μΑ	
Emitter cut-off cur	rent	I _{EBO}	V _{EB} = 5 V, I _C = 0	-	_	1.0	μΑ	
Collector-emitter b	oreakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	50	_	_	V	
DC current gain		h _{FE (1)} (Note)	V _{CE} = 2 V, I _C = 0.5 A	70	_	240		
		h _{FE (2)}	V _{CE} = 2 V, I _C = 1.5 A	40	_	_		
Collector-emitter s	saturation voltage	V _{CE} (sat)	I _C = 1 A, I _B = 0.05 A	_	_	0.5	V	
Base-emitter satu	ration voltage	V _{BE} (sat)	I _C = 1 A, I _B = 0.05 A	_	_	1.2	V	
Transition frequency		f _T	V _{CE} = 2 V, I _C = 0.5 A	_	100	_	MHz	
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _C = 0, f = 1 MHz	_	30	_	pF	
Switching time	Turn-on time	t _{on}	20 µs Input IB1 Output B 1 Output B 1 Output B 2 Output B 2 Output B 3 O V	_	0.1	_		
	Storage time	t _{stg}			1.0	_	μs	
	Fall time	t _f	I _{B1} = −I _{B2} = 0.05 A, duty cycle ≤ 1%	_	0.1	_		

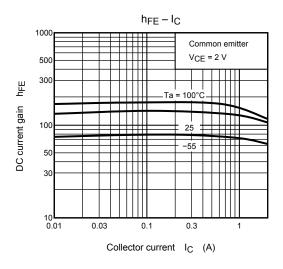
Note: h_{FE} (1) classification O: 70 to 140, Y: 120 to 240

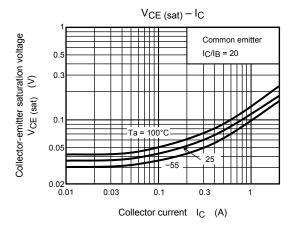
Marking

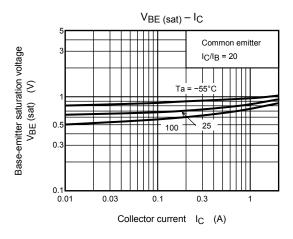


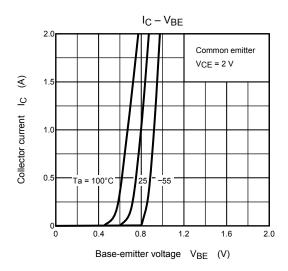
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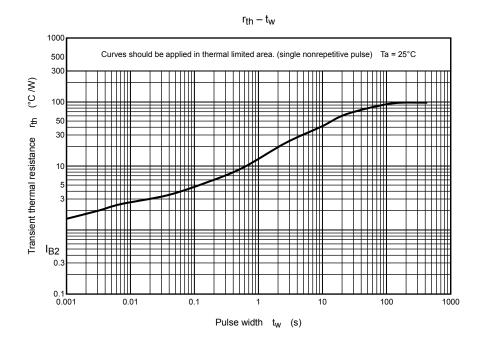


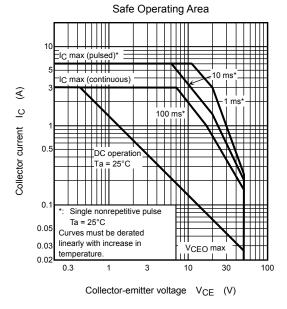


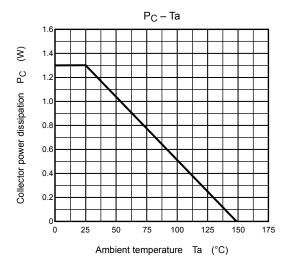




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